



1.25 A sensitive gate SCR

Features

- on-state rms current: 1.25 A
- repetitive peak off-state voltage: 600 V and 800 V
- gate triggering current: 50 and 200 μ A

Applications

- ground fault circuit interrupters
- overvoltage crowbar protection in power supplies
- capacitive ignition circuits

Description

The X02 SCR can be used as the on/off function in applications where topology does not offer high current for gate triggering.

This device is optimized in forward voltage drop and inrush current capabilities for reduced power losses and high reliability in harsh environments.

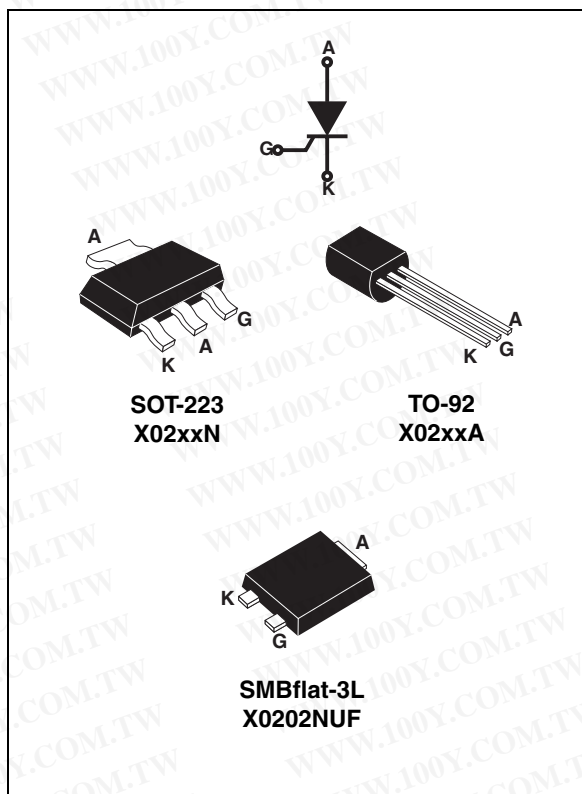


Table 1. Device summary

Order code	Voltage		Sensitivity μ A	Package
	600 V	800 V		
X0202MA	Y		200	TO-92
X0202MN	Y		200	SOT-223
X0202NA		Y	200	TO-92
X0202NN		Y	200	SOT-223
X0205MA	Y		50	TO-92
X0205NA		Y	50	TO-92
X0202NUF		Y	200	SMBflat-3L

1 Characteristics

Table 2. Absolute ratings (limiting values, $T_j = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter		Value	Unit	
$I_{T(RMS)}$	On-state rms current (180 °Conduction angle)	TO-92	$T_L = 63\text{ °C}$	1.25	A
		SOT-223	$T_{tab} = 99\text{ °C}$		
		SMBflat-3L	$T_{tab} = 111\text{ °C}$		
$I_{T(AV)}$	Average on-state current (180 °Conduction angle)	TO-92	$T_L = 63\text{ °C}$	0.8	A
		SOT-223	$T_{tab} = 99\text{ °C}$		
		SMBflat-3L	$T_{tab} = 111\text{ °C}$		
I_{TSM}	Non repetitive surge peak on-state current	$t_p = 8.3\text{ ms}$	$T_j = 25\text{ °C}$	25	A
		$t_p = 10\text{ ms}$		22.5	
I^2t	I^2t Value for fusing	$t_p = 10\text{ ms}$	$T_j = 25\text{ °C}$	2.5	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}, t_r \leq 100\text{ ns}$	$F = 60\text{ Hz}$	$T_j = 125\text{ °C}$	50	$A/\mu s$
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu s$	$T_j = 125\text{ °C}$	1.2	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125\text{ °C}$	0.2	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^{\circ}C$

Table 3. Electrical characteristics ($T_j = 25\text{ °C}$ unless otherwise specified)

Symbol	Test conditions		X0202	X0205	Unit	
I_{GT}	$V_D = 12\text{ V}, R_L = 140\text{ }\Omega$	Min.		20	μA	
		Max.	200	50		
V_{GT}		Max.	0.8		V	
V_{GD}	$V_D = V_{DRM}, R_L = 3.3\text{ k}\Omega, R_{GK} = 1\text{ k}\Omega$	$T_j = 125\text{ °C}$	Min.	0.1		V
V_{RG}	$I_{RG} = 10\text{ }\mu A$		Min.	8		V
I_H	$I_T = 50\text{ mA}, R_{GK} = 1\text{ k}\Omega$		Max.	5		mA
I_L	$I_G = 1\text{ mA}, R_{GK} = 1\text{ k}\Omega$		Max.	6		mA
dV/dt	$V_D = 67\% V_{DRM}, R_{GK} = 1\text{ k}\Omega$	$T_j = 110\text{ °C}$	Min.	10	15	$V/\mu s$

Table 4. Static electrical characteristics

Symbol	Test conditions		X0202	X0205	Unit
V_{TM}	$I_{TM} = 2.5\text{ A}, t_p = 380\text{ }\mu s$	$T_j = 25\text{ °C}$	1.45		V
V_{TO}	Threshold voltage	$T_j = 125\text{ °C}$	0.9		V
R_d	Dynamic resistance		Max.	200	
$I_{DRM} I_{RRM}$	$V_{DRM} = V_{RRM}, R_{GK} = 1\text{ k}\Omega$	$T_j = 25\text{ °C}$	5		μA
		$T_j = 125\text{ °C}$	500		μA

Table 5. Thermal resistances

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction to leads (DC)		TO-92	°C/W
$R_{th(j-t)}$	Junction to tab (DC)		SOT-223	
$R_{th(j-t)}$	Junction to tab (DC)		SMBflat-3L	
$R_{th(j-a)}$	Junction to ambient (DC)	S = 5 cm ²	TO-92	
			SOT-223	
			SMBflat-3L	
			Max.	

Figure 1. Maximum average power dissipation versus average on-state current (full cycle)

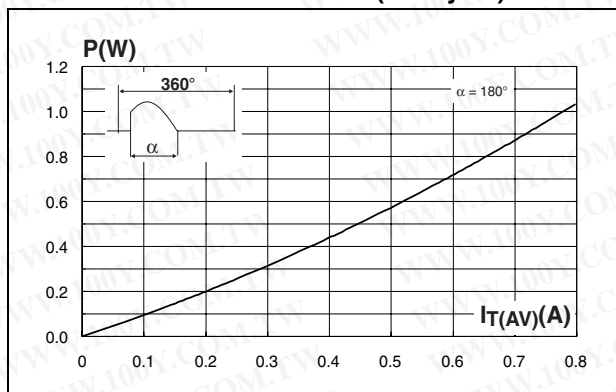


Figure 2. Average and DC on-state current versus tab (SOT-223, SMBflat-3L) or lead (TO-92) temperature

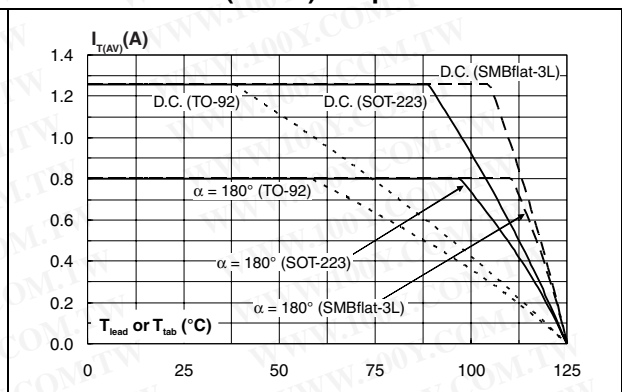


Figure 3. Average and DC on-state current versus ambient temperature

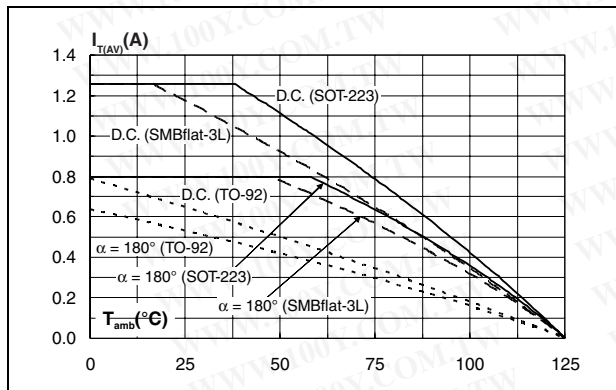


Figure 4. Relative variation of thermal impedance junction to ambient versus pulse duration

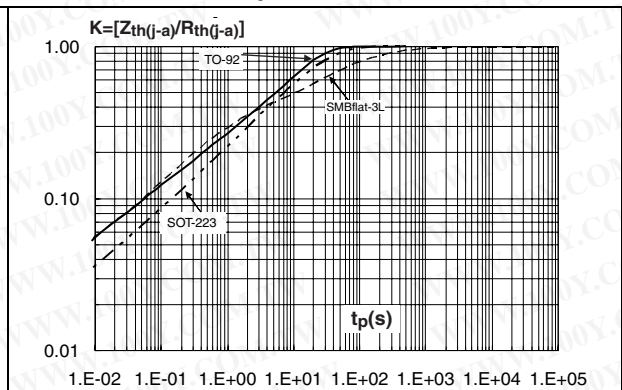


Figure 5. Relative variation of triggering, holding and latching current versus junction temperature

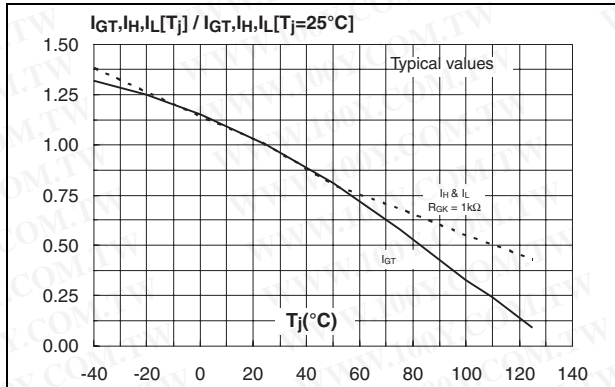


Figure 6. Relative variation of holding current versus gate-cathode resistance (typical values)

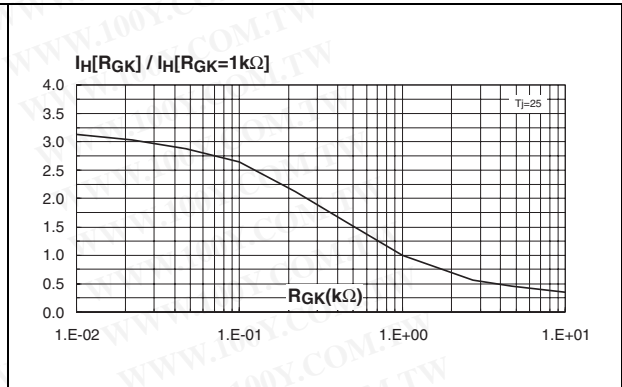


Figure 7. Relative variation of dV/dt immunity versus gate-cathode resistance (typical values)

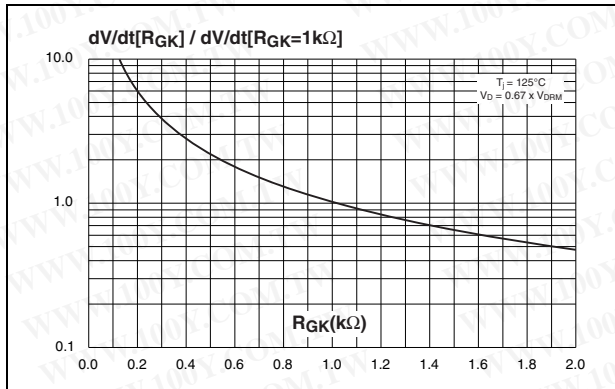


Figure 8. Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values)

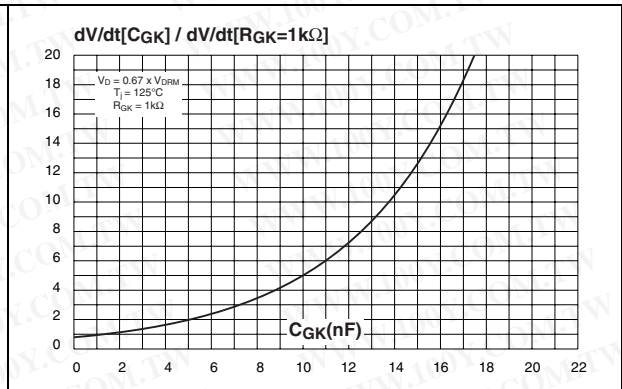


Figure 9. Surge peak on-state current versus number of cycles

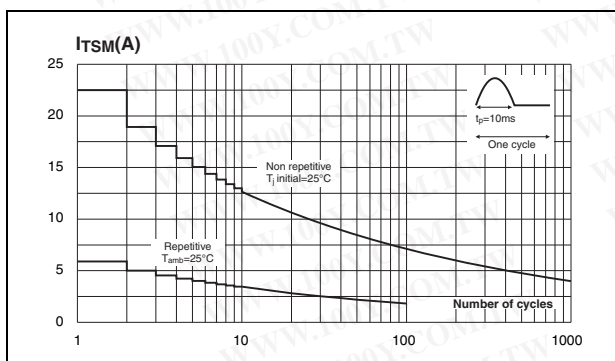


Figure 10. Non repetitive surge peak on state current for a sinusoidal pulse and corresponding value of I²T

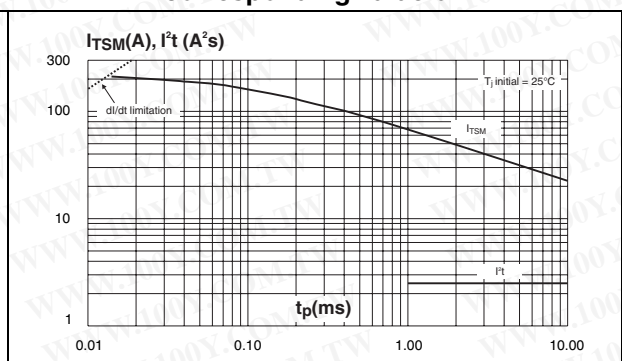
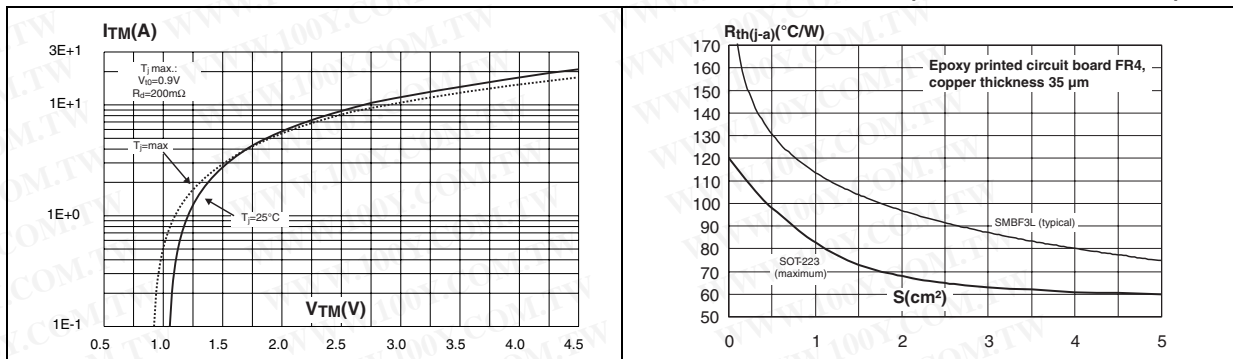
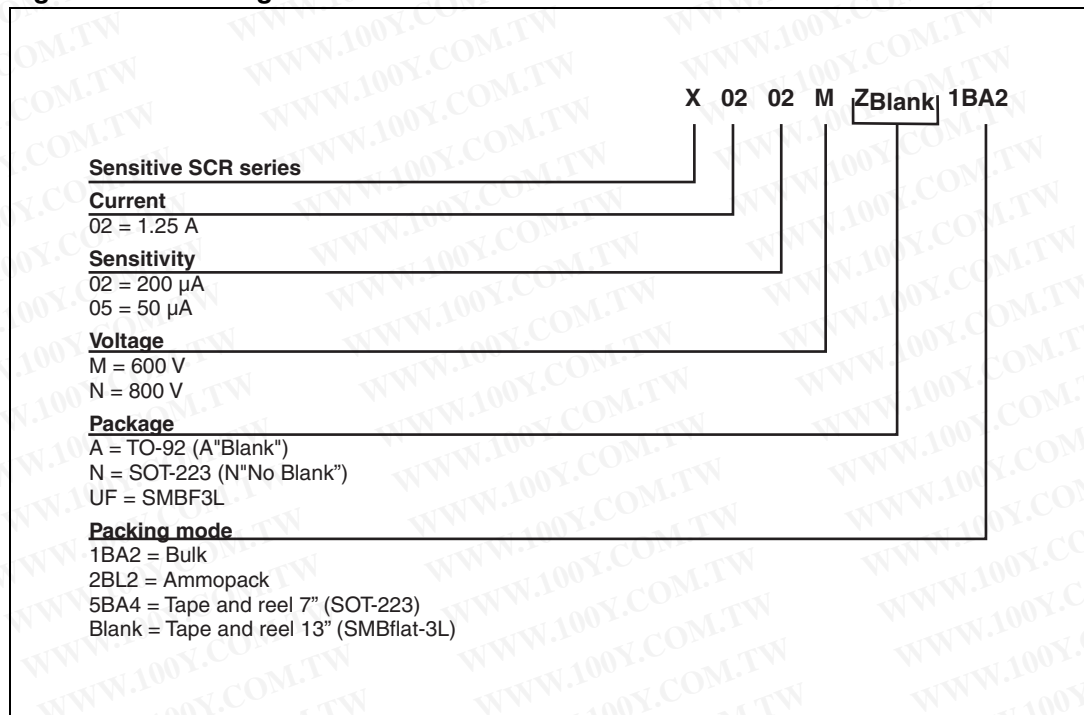


Figure 11. On-state characteristics (maximum values) Figure 12. Thermal resistance junction to ambient versus copper surface under tab (SOT-223, SMBflat-3L)



2 Ordering information scheme

Figure 13. Ordering information scheme



3 Package information

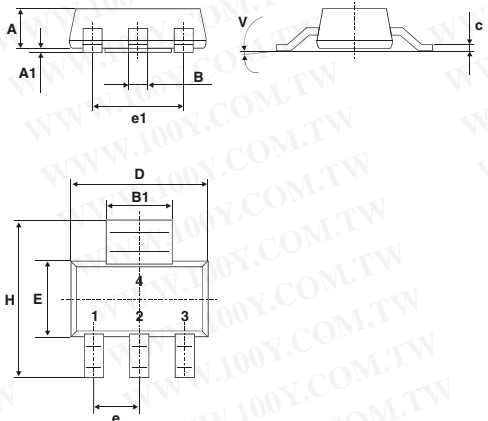
- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 6. TO-92 dimensions

Ref	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		1.35			0.053	
B			4.70			0.185
C		2.54			0.100	
D	4.40			0.173		
E	12.70			0.500		
F			3.70			0.146
a			0.50			0.019

Table 7. SOT-223 dimensions



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.80			0.071
A1		0.02	0.10		0.001	0.004
B	0.60	0.70	0.85	0.024	0.027	0.033
B1	2.90	3.00	3.15	0.114	0.118	0.124
c	0.24	0.26	0.35	0.009	0.010	0.014
D ⁽¹⁾	6.30	6.50	6.70	0.248	0.256	0.264
e		2.3			0.090	
e1		4.6			0.181	
E ⁽¹⁾	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V	10° max					

1. Do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm (0.006inches)

Figure 14. SOT-223 footprint

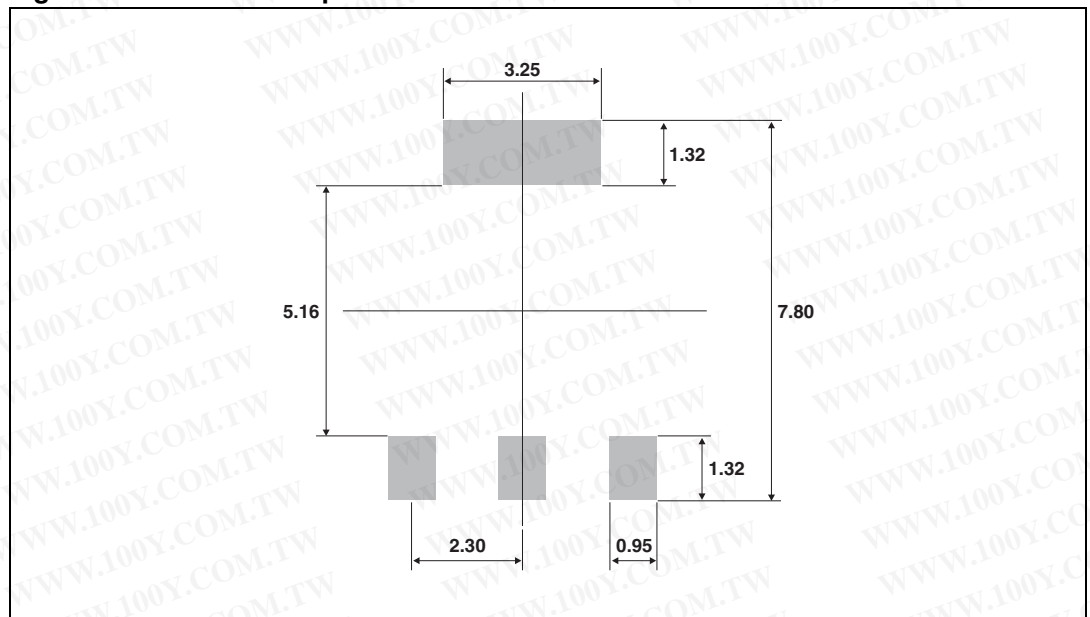
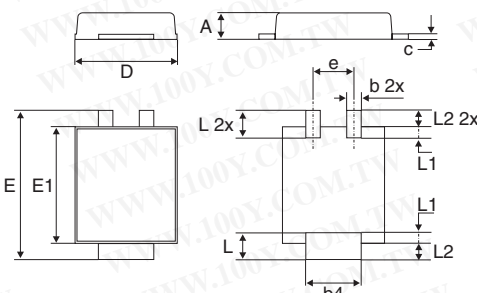


Table 8. SMBflat-3L dimensions



The diagram shows a top-down view of the SMBflat-3L footprint. It features a central rectangular area with two smaller rectangular pads on the top edge. Dimension lines indicate various parameters: A (height of top pad), b (width of top pad), b4 (width of central area), c (width of bottom pad), D (width of central area), E (height of central area), E1 (height of central area excluding top pad), L (height of bottom pad), L1 (height of bottom pad excluding top pad), L2 (height of bottom pad excluding top pad), and e (width of bottom pad).

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.90		1.10	0.035		0.043
b	0.35		0.65	0.014		0.026
b4	1.95		2.20	0.07		0.087
c	0.15		0.40	0.006		0.016
D	3.30		3.95	0.130		0.156
E	5.10		5.60	0.201		0.220
E1	4.05		4.60	0.156		0.181
L	0.75		1.50	0.030		0.059
L1		0.40			0.016	
L2		0.60			0.024	
e		1.60			0.063	

Figure 15. SMBflat-3L footprint dimensions

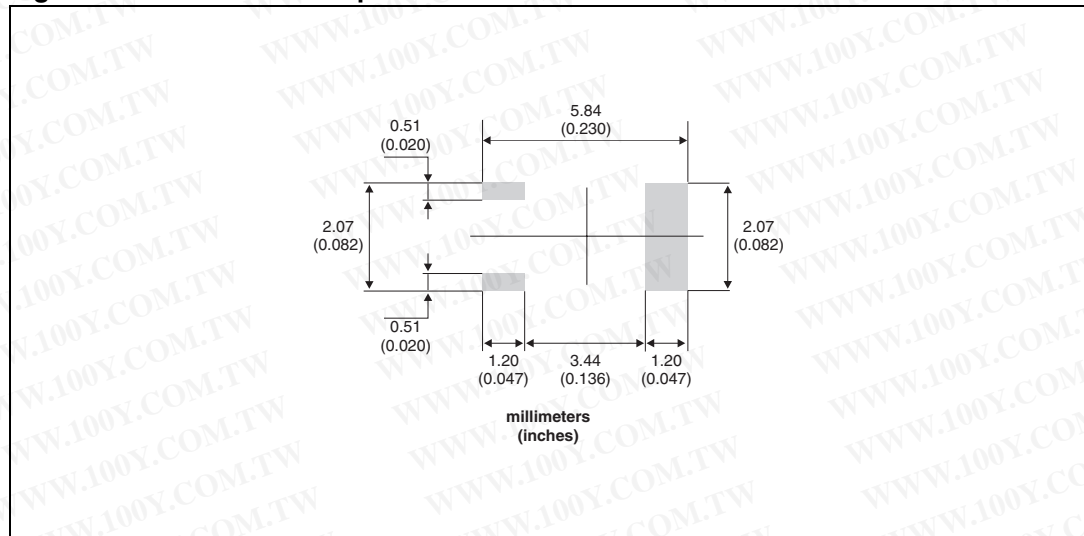
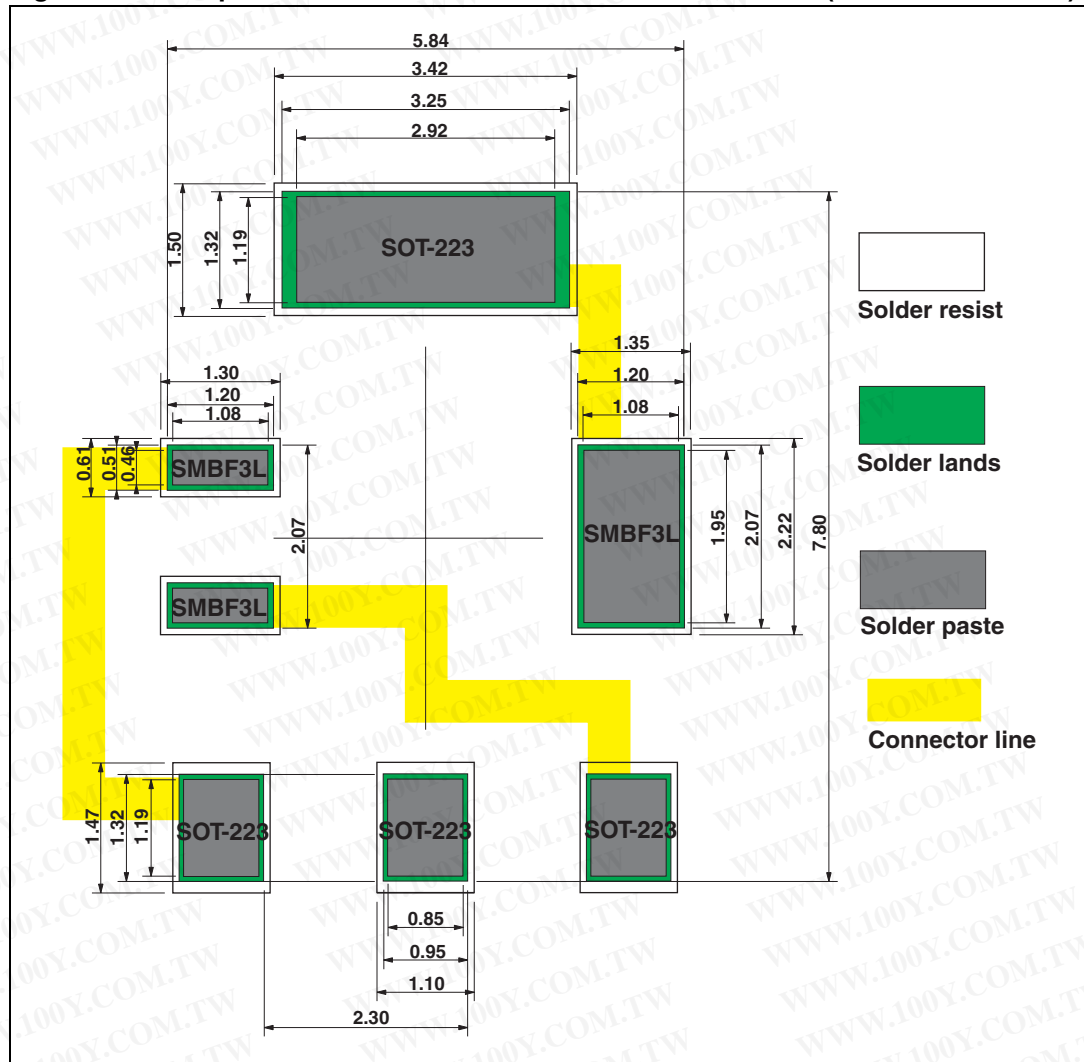


Figure 16. Footprint and connectors for SOT-223 or SMBflat-3L (dimensions in mm)



4 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
X0202MA 1BA2	X0202 MA	TO-92	0.2 g	2500	Bulk
X0202MA 2BL2	X0202 MA	TO-92	0.2 g	2000	Ammopack
X0202MN5BA4	X2M	SOT-223	0.12 g	1000	Tape and reel
X0202NA 1BA2	X0202 NA	TO-92	0.2 g	2500	Bulk
X0202NA 2BL2	X0202 NA	TO-92	0.2 g	2000	Ammopack
X0202NN5BA4	X2N	SOT-223	0.12 g	1000	Tape and reel
X0205MA 1BA2	X0205 MA	TO-92	0.2 g	2500	Bulk
X0205MA 2BL2	X0205 MA	TO-92	0.2 g	2000	Ammopack
X0205NA 1BA2	X0205 NA	TO-92	0.2 g	2500	Bulk
X0202NUF	X2N	SMBflat-3L	46.914 mg	5000	Tape and reel

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
Sep-2000	3	Previous issue
14-Jan-2011	4	Added SMBflat-3L package and ECOPACK statement.

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
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